



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: )  
 Taketomi ASAMI et al. )  
 Application No.: 10/792,132 ) Examiner: Joseph H Nguyen  
 Filed: March 4, 2004 ) Group Art Unit: 2815  
 For: SEMICONDUCTOR DEVICE AND )  
 METHOD OF MANUFACTURING THE SAME )

VERIFICATION OF TRANSLATION

Commissioner for Patents  
 P.O.Box 1450  
 Alexandria, VA 22313-1450

Sir:

I, Yumiko Takekoshi, C/O Semiconductor Energy Laboratory Co., Ltd. 398, Hase, Atsugi-shi, Kanagawa-ken 243-0036 Japan, a translator, herewith declare:

that I am well acquainted with both the Japanese and English Languages;

that I am the translator of the attached translation of the Japanese Patent Application No. 2000-234913 filed on August 2, 2000; and

that to the best of my knowledge and belief the followings is a true and correct translation of the Japanese Patent Application No. 2000-234913 filed on August 2, 2000.

I further declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Date: this 8th day of August 2005

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Name: Yumiko Takekoshi



[Name of Document]

Patent Application

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August 2, 2000

[Attention]

Commissioner, Patent Office Kouzou OIKAWA

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[Indication of Handlings]

25 [Number of Prepayment Note] 002543

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[List of Attachment]

[Attachment] Specification 1

[Attachment] Drawing 1

5 [Attachment] Abstract 1

[Proof] Required

[Name of Document] Specification

[Title of the Invention]

10 SEMICONDUCTOR FILM AND SEMICONDUCTOR DEVICE,  
SEMICONDUCTOR FILM AND METHOD OF MANUFACTURING  
SEMICONDUCTOR DEVICE

[Scope of Claim]

15 [Claim 1]

A semiconductor film having a crystal structure with a composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below, characterized in that

the {101} plane in the semiconductor film reaches 30% or more of all the lattice

20 planes detected by Electron backscatter diffraction.

[Claim 2]

A semiconductor film having a polycrystal structure with the composition ratio of germanium to silicon being 0.1 atomic percent or more and 10 atomic percent or below, characterized in that

25 the {101} plane in the semiconductor film reaches 30% or more of all the lattice